

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	229289	(CMP (chemical near5 polish\$3)) or (polish\$3 planarization planariz\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:13
L2	13227	1 and selectivity	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:14
L3	2269	2 and slurry	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:14
L4	699	3 and (polysilicon (polycrystalline near5 silicon))	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:14
L5	679	4 and oxide	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:03
L6	137	5 and ((polysilicon (polycrystalline near5 silicon)) same oxide same selectivity)	US-PGPU B; USPAT; USOCR	OR	ON	2005/02/20 11:07
L8	122309	(CMP (chemical near5 polish\$3)) or (polish\$3 planarization planariz\$3)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/20 11:13
L9	614	8 and selectivity	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/20 11:14
L10	181	9 and slurry	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/20 11:14
L11	18	10 and (polysilicon (polycrystalline near5 silicon))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/02/20 11:14